1. General description

PNP/PNP general-purpose double transistors in a leadless ultra small DFN1412-6 (SOT1268) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: BC847RA
NPN/PNP complement: BC847RAPN

2. Features and benefits

- Reduces component count
- Reduces pick and place costs
- Low package height of 0.5 mm
- AEC-Q101 qualified

3. Applications

- · General-purpose switching and amplification
- · Mobile applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	Per transistor						
V _{CEO}	collector-emitter voltage	open base		-	-	-45	V
I _C	collector current			-	-	-100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-200	mA
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C		200	-	450	



45 V, 100 mA PNP/PNP general-purpose double transistors

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		6 5 4
2	B1	base TR1	$\begin{bmatrix} 1 \\ 7 \end{bmatrix}$	
3	C2	collector TR2	5	(TR1) TR2)
4	E2	emitter TR2		
5	B2	base TR2	3 8 4	1 2 3
6	C1	collector TR1		sym018
7	C1	collector TR1	Transparent top view	
8	C2	collector TR2	DFN1412-6 (SOT1268)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BC857RA	DFN1412-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body: 1.4 mm x 1.2 mm x 0.47 mm	SOT1268			

7. Marking

Table 4. Marking codes

Type number	Marking code
BC857RA	A6

45 V, 100 mA PNP/PNP general-purpose double transistors

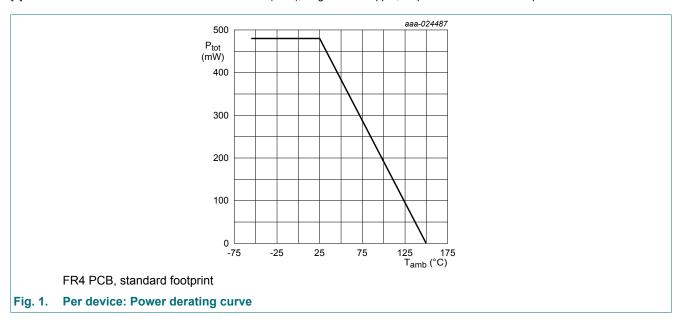
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or		•			
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-45	V
V_{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-200	mA
I _{BM}	peak base current			-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	325	mW
Per device			•	'	•	'
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	480	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



45 V, 100 mA PNP/PNP general-purpose double transistors

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	385	K/W
Per device	Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	261	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

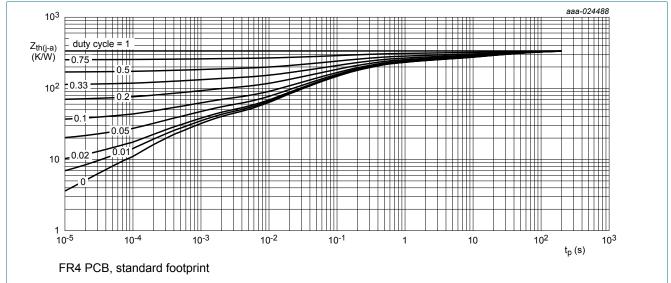


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

45 V, 100 mA PNP/PNP general-purpose double transistors

10. Characteristics

Table 7. Characteristics

Parameter	Conditions	Min	Тур	Max	Unit
or			'		
collector-base cut-off	V _{CB} = -30 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-15	nA
current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	-5	μΑ
emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
DC current gain	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C	200	-	450	
collector-emitter saturation voltage	I_C = -10 mA; I_B = -0.5 mA; T_{amb} = 25 °C	-	-	-100	mV
	I_C = -100 mA; I_B = -5 mA; T_{amb} = 25 °C	-	-	-300	mV
base-emitter saturation voltage	I_C = -10 mA; I_B = -0.5 mA; T_{amb} = 25 °C	-	-760	-	mV
	I_C = -100 mA; I_B = -5 mA; T_{amb} = 25 °C	-	-900	-	mV
base-emitter voltage	$V_{CE} = -5 \text{ V; } I_{C} = -2 \text{ mA; } T_{amb} = 25 \text{ °C}$	-600	-660	-725	mV
	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	-710	-820	mV
collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	4	pF
emitter capacitance	V_{EB} = -0.5 V; I_{C} = 0 A; I_{c} = 0 A; I_{c} = 0 A; I_{c} = 1 MHz; I_{c} I_{c} = 25 °C	-	10	-	pF
transition frequency	V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	100	-	-	MHz
noise figure	V_{CE} = -5 V; I_{C} = -0.2 mA; R_{S} = 2 k Ω ; f = 1 kHz; B = 200 Hz; T_{amb} = 25 °C	-	-	10	dB
	collector-base cut-off current emitter-base cut-off current DC current gain collector-emitter saturation voltage base-emitter saturation voltage base-emitter voltage collector capacitance emitter capacitance transition frequency	collector-base cut-off current $ \begin{array}{c} \text{collector-base cut-off current} \\ \text{current} \\ \end{array} \begin{array}{c} \text{Collector-base cut-off current} \\ \text{V}_{CB} = -30 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{amb} = 25 ^{\circ}\text{C} \\ \text{V}_{CB} = -30 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{j} = 150 ^{\circ}\text{C} \\ \text{V}_{CB} = -30 \text{ V}; \text{ I}_{C} = 0 \text{ A}; \text{ T}_{amb} = 25 ^{\circ}\text{C} \\ \text{V}_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}; \text{ T}_{amb} = 25 ^{\circ}\text{C} \\ \text{Collector-emitter} \\ \text{saturation voltage} \\ \text{I}_{C} = -10 \text{ mA}; \text{ I}_{B} = -0.5 \text{ mA}; \text{ T}_{amb} = 25 ^{\circ}\text{C} \\ \text{I}_{C} = -100 \text{ mA}; \text{ I}_{B} = -5 \text{ mA}; \text{ T}_{amb} = 25 ^{\circ}\text{C} \\ \text{I}_{C} = -100 \text{ mA}; \text{ I}_{B} = -0.5 \text{ mA}; \text{ T}_{amb} = 25 ^{\circ}\text{C} \\ \text{I}_{C} = -100 \text{ mA}; \text{ I}_{B} = -5 \text{ mA}; \text{ T}_{amb} = 25 ^{\circ}\text{C} \\ \text{V}_{CE} = -5 \text{ V}; \text{ I}_{C} = -2 \text{ mA}; \text{ T}_{amb} = 25 ^{\circ}\text{C} \\ \text{V}_{CE} = -5 \text{ V}; \text{ I}_{C} = -10 \text{ mA}; \text{ T}_{amb} = 25 ^{\circ}\text{C} \\ \text{V}_{CE} = -5 \text{ V}; \text{ I}_{C} = -10 \text{ mA}; \text{ T}_{amb} = 25 ^{\circ}\text{C} \\ \text{Collector capacitance} \\ \text{V}_{CB} = -10 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ I}_{e} = 0 \text{ A}$	$ \begin{array}{c} \text{collector-base cut-off} \\ \text{current} \\ \end{array} \begin{array}{c} \text{Collector-base cut-off} \\ \text{current} \\ \end{array} \begin{array}{c} \text{V}_{CB} = -30 \text{ V}; \ I_{E} = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \hline \text{V}_{CB} = -30 \text{ V}; \ I_{E} = 0 \text{ A}; \ T_{j} = 150 \text{ °C} \\ \end{array} \begin{array}{c} - \\ \text{emitter-base cut-off} \\ \text{current} \\ \end{array} \begin{array}{c} \text{V}_{EB} = -5 \text{ V}; \ I_{C} = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \end{array} \begin{array}{c} - \\ \text{Collector-emitter} \\ \text{saturation voltage} \\ \end{array} \begin{array}{c} \text{I}_{C} = -10 \text{ mA}; \ I_{B} = -0.5 \text{ mA}; \ T_{amb} = 25 \text{ °C} \\ \hline \text{I}_{C} = -100 \text{ mA}; \ I_{B} = -0.5 \text{ mA}; \ T_{amb} = 25 \text{ °C} \\ \hline \text{I}_{C} = -100 \text{ mA}; \ I_{B} = -0.5 \text{ mA}; \ T_{amb} = 25 \text{ °C} \\ \hline \text{I}_{C} = -100 \text{ mA}; \ I_{B} = -0.5 \text{ mA}; \ T_{amb} = 25 \text{ °C} \\ \hline \text{I}_{C} = -100 \text{ mA}; \ I_{B} = -0.5 \text{ mA}; \ T_{amb} = 25 \text{ °C} \\ \hline \text{V}_{CE} = -5 \text{ V}; \ I_{C} = -2 \text{ mA}; \ T_{amb} = 25 \text{ °C} \\ \hline \text{V}_{CE} = -5 \text{ V}; \ I_{C} = -10 \text{ mA}; \ T_{amb} = 25 \text{ °C} \\ \hline \text{Collector capacitance} \\ \hline \text{V}_{CB} = -10 \text{ V}; \ I_{E} = 0 \text{ A}; \ I$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

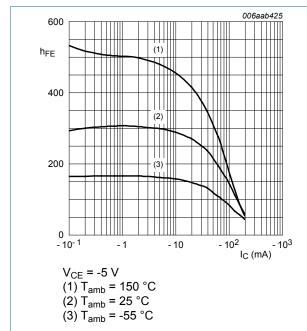


Fig. 3. DC current gain as a function of collector current; typical values

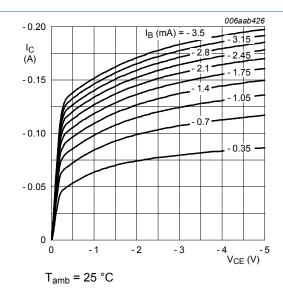


Fig. 4. Collector current as a function of collectoremitter voltage; typical values

45 V, 100 mA PNP/PNP general-purpose double transistors

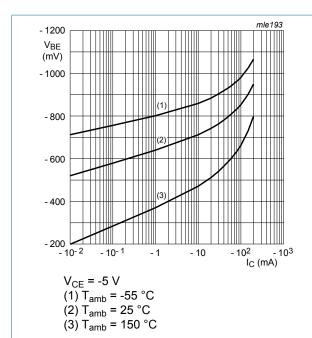
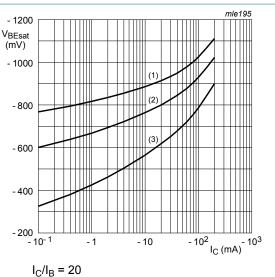


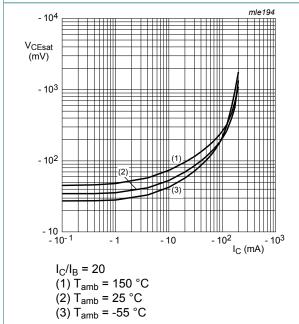
Fig. 5. Base-emitter voltage as a function of collector current; typical values



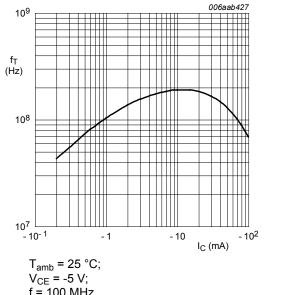
$$I_{C}/I_{B} = 20$$

(1) $T_{amb} = -55 \,^{\circ}\text{C}$
(2) $T_{amb} = 25 \,^{\circ}\text{C}$
(3) $T_{amb} = 150 \,^{\circ}\text{C}$

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values



Collector-emitter saturation voltage as a Fig. 7. function of collector current; typical values



V_{CE} = -5 V; f = 100 MHz

Fig. 8. Transition frequency as a function of collector current; typical values

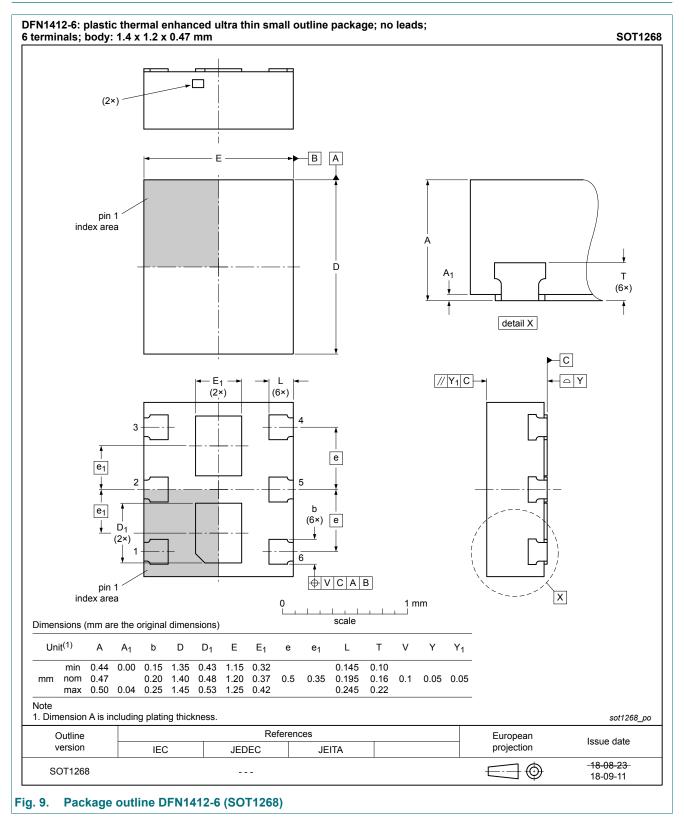
11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

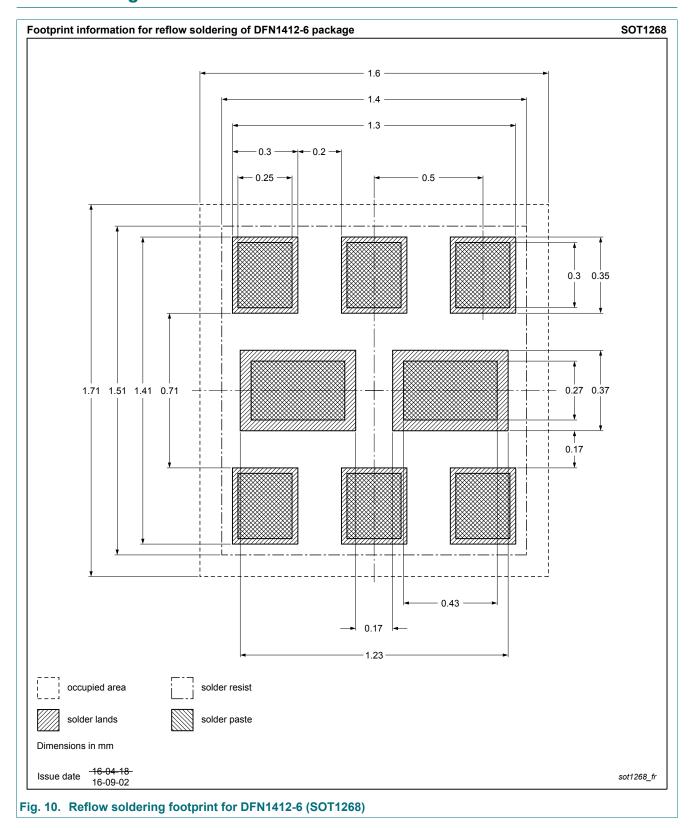
45 V, 100 mA PNP/PNP general-purpose double transistors

12. Package outline



45 V, 100 mA PNP/PNP general-purpose double transistors

13. Soldering



DC057D4

45 V, 100 mA PNP/PNP general-purpose double transistors

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
BC857RA v.2	20180914	Product data sheet	-	BC857RA v.1			
Modifications:	Package outline drawing updated: Unit T added						
BC857RA v.1	20170607	Product data sheet	-	-			

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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45 V, 100 mA PNP/PNP general-purpose double transistors

Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	4
10. Characteristics	5
11. Test information	6
12. Package outline	7
13. Soldering	8
14. Revision history	9
15. Legal information	10

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11 / 11

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